

AMG8205A

Common Drain Dual N-Channel 2.5V (G-S) MOSFET



Features

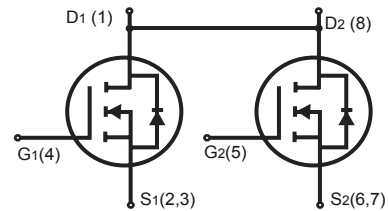
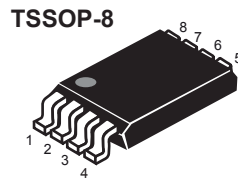
- High performance trench technology
- Low ON-resistance
- 2.5V gate drive
- Common drain configuration
- Low profile surface mount package
- Lead (Pb) free product

Product Summary

V _{DS} (V)	I _D (A)	R _{DS(ON)} (mΩ) Max
20V	6A	25 @V _{GS} = 4.0V
		37 @V _{GS} = 2.5V

Applications

- Li-ion battery pack
- Load switch
- Power management



Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous @ T _C = 25°C	I _D	6	A
-Pulsed ^b	I _{DM}	30	A
Drain-Source Diode Forward Current ^a	I _S	1.7	A
Maximum Power Dissipation ^a	P _D	2	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^a	R _{θJA}	83	°C/W
--	------------------	----	------

Electrical Characteristics (TA = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250 μA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =250 μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.0V, I _D =4A		21	25	mΩ
		V _{GS} =2.5V, I _D =3A		27	37	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =4A		13		S
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _D =1A		0.8	1.2	V

Dynamic

Input Capacitance	C _{ISS}	V _{DS} =8V V _{GS} =0V f=1.0MHz		1180		pF
Output Capacitance	C _{OSS}			260		
Reverse Transfer Capacitance	C _{RSS}			195		
Turn-On Delay Time	t _{D(ON)}	V _D =10V, I _D =1A, V _{GEN} =4.5V, R _{GEN} =10Ω, R _L =10Ω		32		ns
Rise Time	t _r			8		
Turn-Off Delay Time	t _{D(OFF)}			75		
Fall Time	t _f			30		
Total Gate Charge	Q _g	V _{DS} =10V, I _D =4A, V _{GS} =4.5V		16		nC
Gate-Source Charge	Q _{gs}			2.5		
Gate-Drain Charge	Q _{gd}			4		

Notes:

- Surface Mounted on FR4 Board, t ≤ 10 sec.
- Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

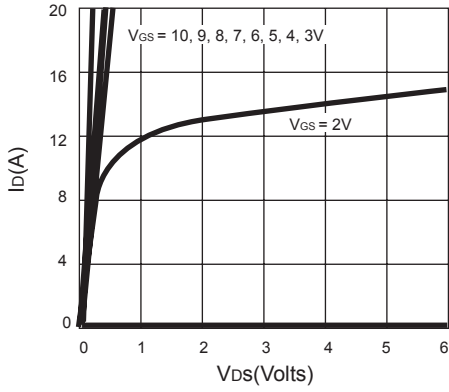


Figure 1. On-Regions Characteristics

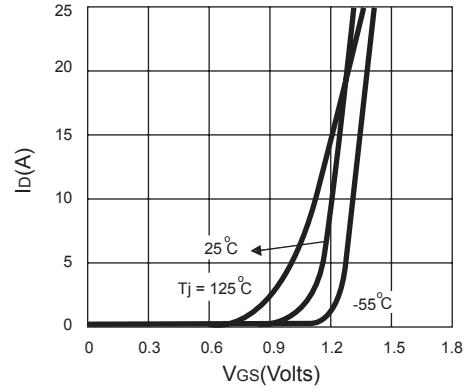


Figure 2. Transfer Characteristics

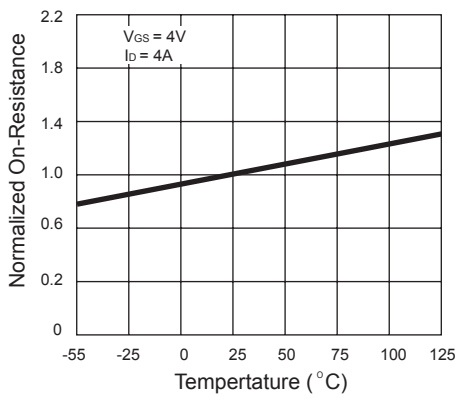


Figure 3. On-Resistance vs. Junction Temperature

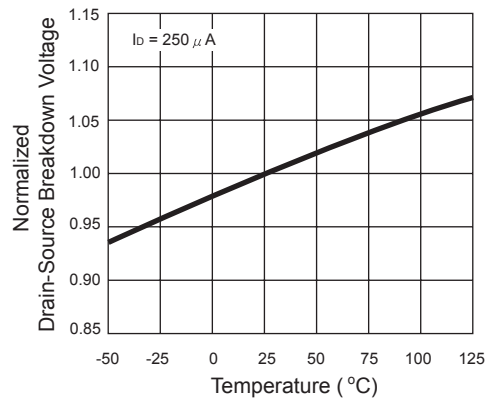


Figure 4. Drain-Source Breakdown Voltage vs. Temperature

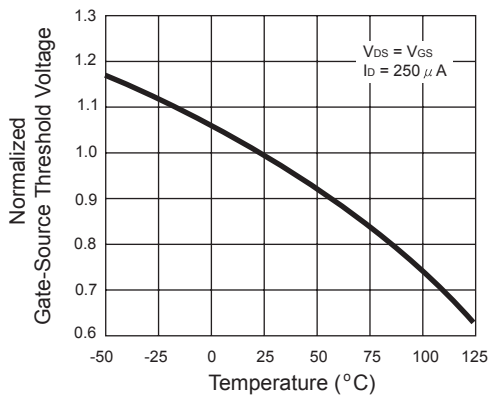


Figure 5. Gate Threshold vs. Junction Temperature

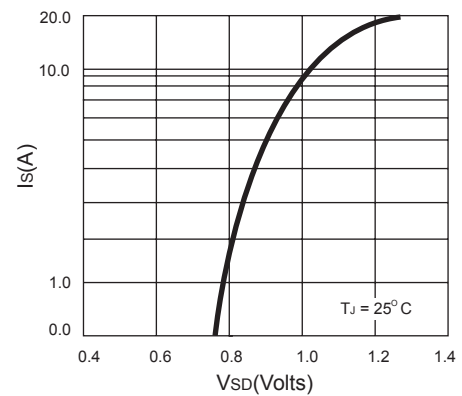


Figure 6. Body Diode Characteristics

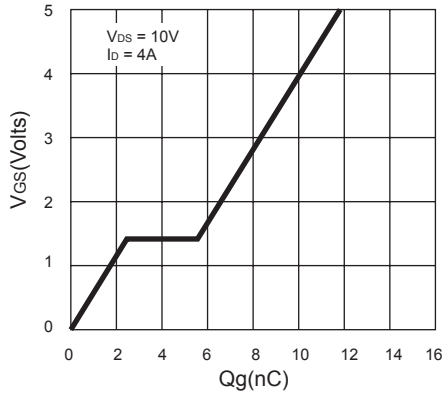


Figure 7. Gate-Charge Characteristics

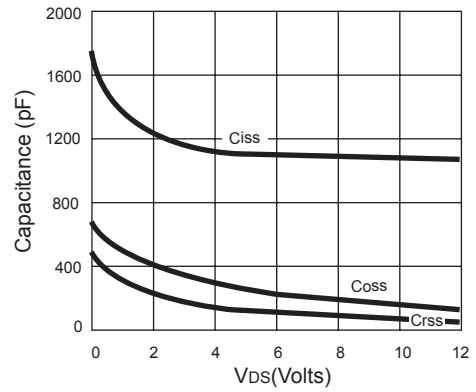


Figure 8. Capacitance Characteristics

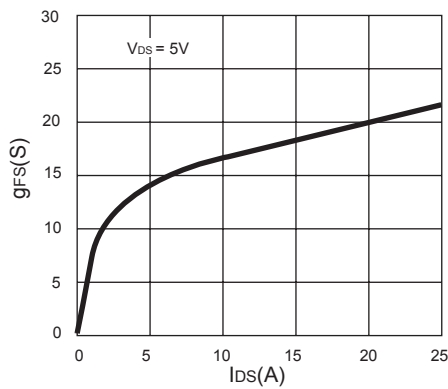


Figure 9. Transconductance vs. Drain Current

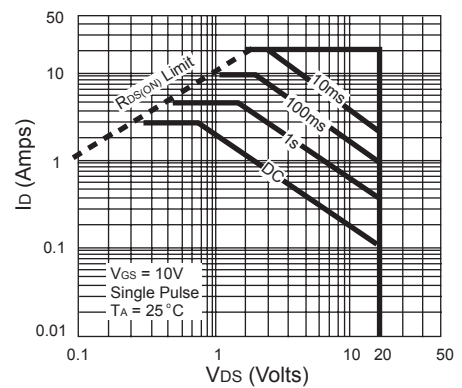


Figure 10. Maximum Forward Biased Safe Operating Area

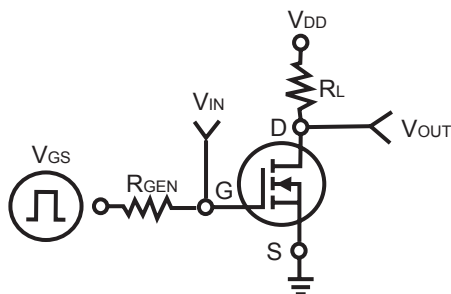


Figure 11. Switching Test Circuit

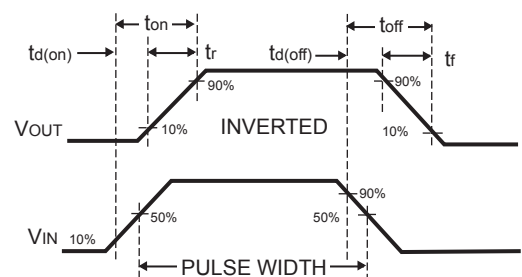


Figure 12. Switching Waveforms

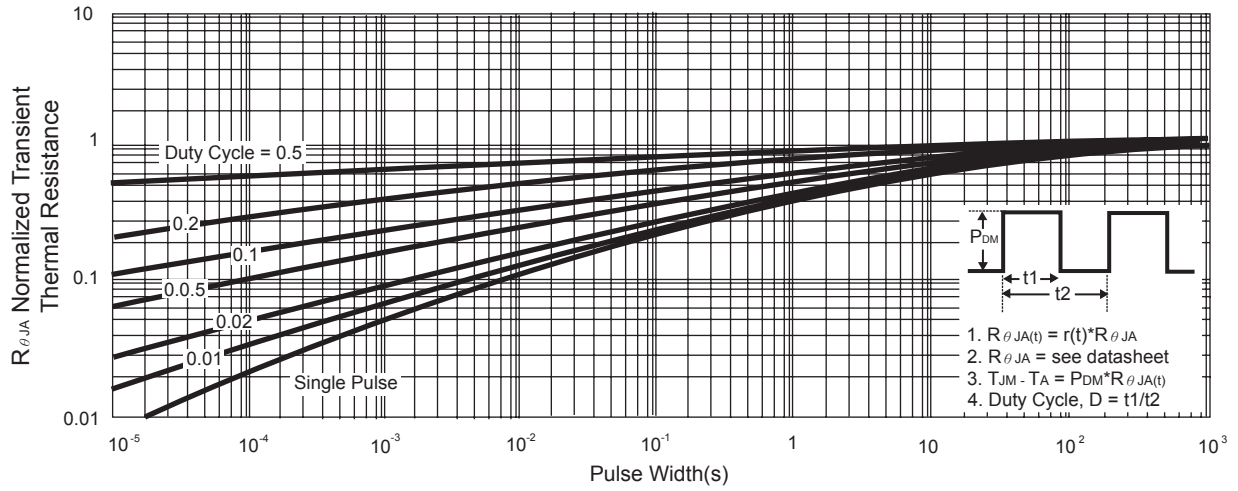


Figure 13. Normalized Maximum Transient Thermal Impedance